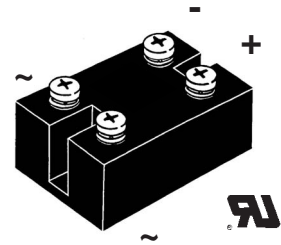
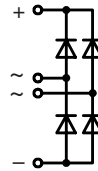


Single Phase Rectifier Bridge

$I_{dAVM} = 107 \text{ A}$
 $V_{RRM} = 1200-1800 \text{ V}$

V_{RSM} V	V_{RRM} V	Type
900	800	VBO 105-08NO7
1200	1200	VBO 105-12NO7
1400	1400	VBO 105-14NO7
1600	1600	VBO 105-16NO7
1800	1800	VBO 105-18NO7*

* delivery time on request



Symbol	Conditions	Maximum Ratings	
I_{dAVM}	$T_C = 85^\circ\text{C}$, module	107	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	1500 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	1650 A
I^2t	$T_{VJ} = T_{VJM}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	1350 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	1500 A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	11250 A ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	11300 A ² s
T_{VJ}		-40...+150	$^\circ\text{C}$
		150	$^\circ\text{C}$
T_{VJM}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$	2500 V~
		$t = 1 \text{ s}$	3000 V~
M_d	Mounting torque (M5) Terminal connection torque (M5)	5 \pm 15%	Nm
		44 \pm 15%	lb.in.
		5 \pm 15%	Nm
		44 \pm 15%	lb.in.
Weight	typ.	225	g

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E 72873

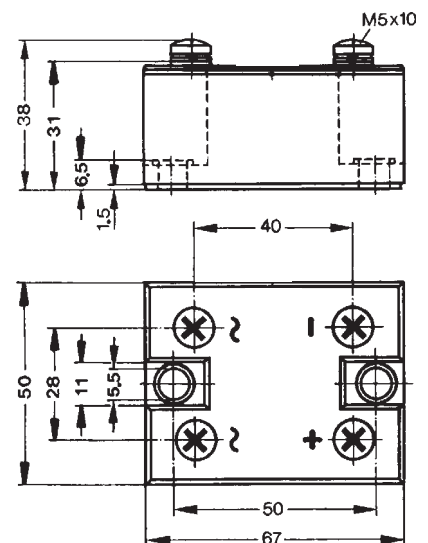
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Conditions	Characteristic Values	
I_R	$V_R = V_{RRM}$; $V_R = V_{RRM}$;	$T_{VJ} = 25^\circ\text{C}$	$\leq 0.3 \text{ mA}$
		$T_{VJ} = T_{VJM}$	$\leq 8.0 \text{ mA}$
V_F	$I_F = 150 \text{ A}$;	$T_{VJ} = 25^\circ\text{C}$	$\leq 1.6 \text{ V}$
V_{T0}	For power-loss calculations only		0.8 V
r_T	$T_{VJ} = T_{VJM}$		5 m Ω
R_{thJC}	per diode; 180° per module; 180°		0.83 K/W
			0.138 K/W
R_{thJK}	per diode; 180° per module; 180°		1.13 K/W
			0.188 K/W

Data according to IEC 60747 refer to a single diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

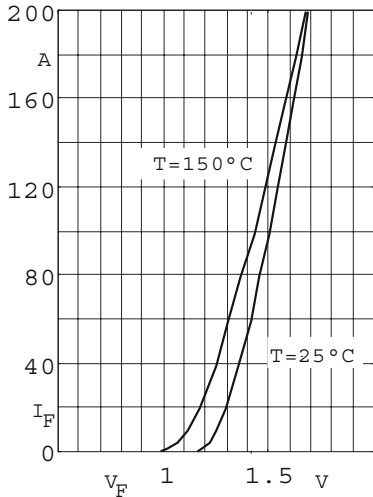


Fig. 1 Forward current versus voltage drop per diode

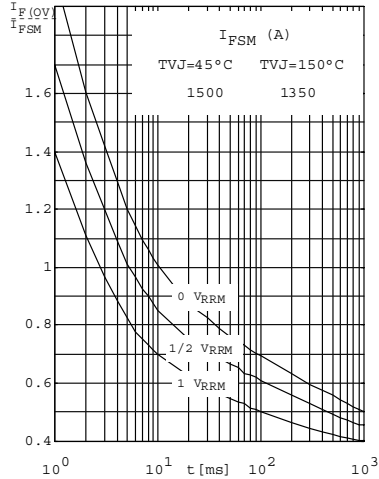


Fig. 2 Surge overload current per diode I_{FSM} : Crest value. t : duration

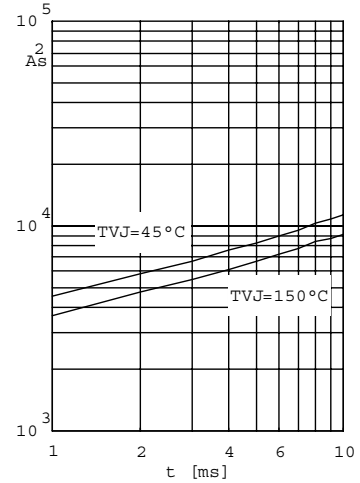


Fig. 3 $\int i^2 dt$ versus time (1-10ms) per diode or thyristor

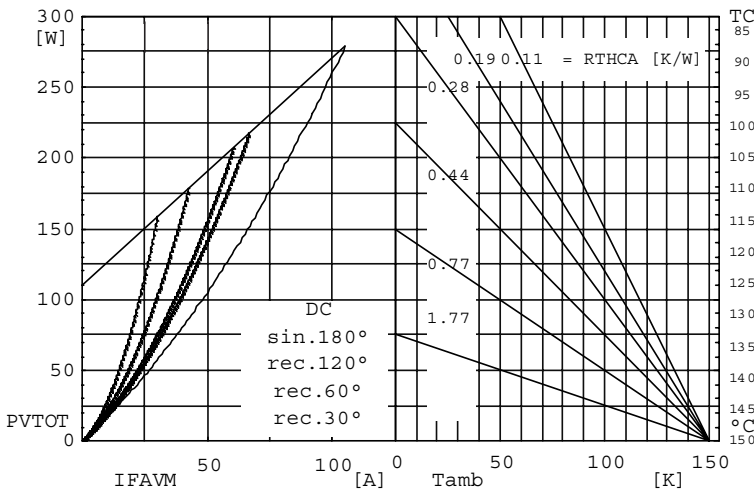


Fig. 4 Power dissipation versus direct output current and ambient temperature

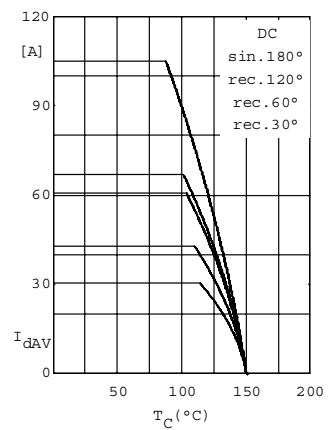


Fig.5 Maximum forward current at case temperature

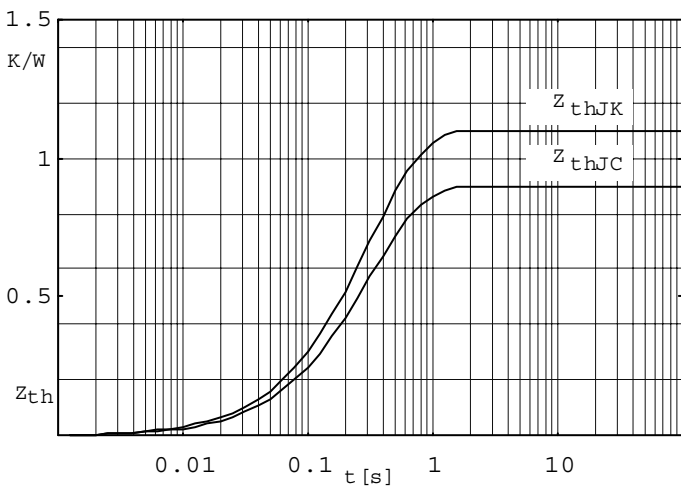


Fig. 6 Transient thermal impedance per diode or thyristor, calculated